

TWO-STAGE LOAD FOR PROCESSING BOTH SIDES OF A WAFERAbstract of the Disclosure

Disclosed herein is an apparatus and method for treating the frontside and backside of a semiconductor substrate with a process gas. A reactor chamber is equipped with a first load platform configured to permit the access of a process gas to both sides of a substrate. In some embodiments, the apparatus also comprises a second load platform configured for further processing the frontside of the substrate. The substrate is loaded on the first load platform and processed on both sides, then moved to the second load platform and processed on one side.

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